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Crystal Phase Quantum Well Emission with Digital Control


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ABSTRACT: One of the major challenges in the growth of quantum well and quantum dot heterostructures is the realization of atomically sharp interfaces. Nanowires provide a new opportunity to engineer the band structure as they facilitate the controlled switching of the crystal structure between the zinc-blende (ZB) and wurtzite (WZ) phases. Such a crystal phase switching results in the formation of crystal phase quantum wells (CPQWs) and quantum dots (CPQDs). For GaP CPQWs, the inherent electric fields due to the discontinuity of the spontaneous polarization at the WZ/ZB junctions lead to the confinement of both types of charge carriers at the opposite interfaces of the WZ/ZB/WZ structure. This confinement leads to a novel type of transition across a ZB flat plate barrier. Here, we show digital tuning of the visible emission of WZ/ZB/WZ CPQWs in a GaP nanowire by changing the thickness of the ZB barrier. The energy spacing between the sharp emission lines is uniform and is defined by the addition of single ZB monolayers. The controlled growth of identical quantum wells with atomically flat interfaces at predefined positions featuring digitally tunable discrete emission energies may provide a new route to further advance entangled photons in solid state quantum systems.

KEYWORDS: Semiconductor nanowire, gallium phosphide, crystal phase quantum well, spontaneous polarization, photoluminescence
microcrystals and nanowires made of nitride-based semiconductors. In our WZ/ZB/WZ structures, the lengths $L_{\text{ZB}}$ of the ZB segments are much shorter than the lateral dimensions, resulting essentially in a simple parallel plate capacitor. Thus, the polarization sheet charge density $\sigma$ can be estimated as

$$\sigma = \frac{\Delta V \varepsilon_{\text{eff}}}{L_{\text{ZB}}}$$

where $\Delta V$ is the potential difference across the plate capacitor, $\varepsilon$ is the dielectric constant of the material, and $\varepsilon_0$ is the permittivity of free space. The energy shift $\Delta E$ for changing the thickness of the capacitor with a single ZB monolayer is $\Delta E = \Delta V / q$, where $q$ is the elementary charge. This relation results in a discrete red-shift (blue-shift) $\Delta E$ of the emission energy upon the addition (removal) of a single ZB monolayer.

Here, we demonstrate digital tuning of the GaP CPQW emission energy across a spectral range of 75 meV by varying the thickness of the ZB segment. The correlation between photoluminescence measurements and band structure simulations shows that the strong polarization field in GaP induces carrier confinement in the WZ section of the CPQW. The presence of atomically sharp interfaces results in emission line widths well below conventional III–V QW heterostructures. Therefore, the possibility to tailor the growth of WZ/ZB homojunctions in nanowires and thereby to digitally tune their emission energies provides a new tool in the design of solid-state

Figure 1. (a) Plot of the spontaneous polarization fields in III–V semiconductors. The dark blue areas are the values predicted from DFT, while the dark red areas are the values determined from experimental measurements. (b) Calculated band diagram for a CPQW in GaP with 5 ZB MLs using 1D Schrödinger–Poisson simulations. The dashed lines indicate the normalized wave functions for electrons (dark blue) and holes (dark red). Curves are shifted to allow easier comparison. (c) Enlarged view of panel b showing a capacitor-like charge configuration where the sheet of polarization charges and the related QCSE are sketched. (d) Digital tuning of the CPQW transition energy for increasing ZB thicknesses of 5, 6, and 7 MLs. By adding (removing) one monolayer, the resulting transition will be decreased (increased) by an amount of $\Delta E$. 

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quantum emitters in small diameter nanowires featuring true QD emission.

In the WZ unit cell, the bond length between the Ga and P atoms along the (0001) axis (c-axis) is determined as a fraction $u$ of the lattice parameter $c$, where $u$ is called the internal cell parameter. In an ideal WZ unit cell with tetrahedral bonds, $u = 3/8 = 0.375$, and the resulting spontaneous polarization $P_{\text{SP}}$ is equal to zero, which corresponds to the situation in the ZB unit cell. In WZ GaP nanowires, the measured value for the internal parameter is $u = 0.37385 \pm 0.00017$, resulting in the prediction of a fairly large polarization $P_{\text{SP}}^{\text{GaP}} = 9 \text{ mC/m}^2$ along the c-axis. For comparison, calculations by density functional theory predict a value of $P_{\text{SP}}^{\text{ZnSe}} = 3 \text{ mC/m}^2$, which is still higher than in other III–V semiconductors like GaAs, InAs, or InP, as summarized in Figure 1a. Similarly, a significant spontaneous polarization with opposite sign ($u > 3/8$) is known from nitride-based materials.

As discussed above, the interface charges at the WZ/ZB/WZ junctions can be treated as a parallel plate capacitor to derive the polarization field responsible for the change in emission energy per monolayer (ML). A more precise estimation of the evolution of the emission energy with ZB thickness can be performed using one-dimensional (1D) Schrödinger–Poisson calculations for the CPQWs along the c-axis (see Supporting Information S1 for more details). We note that, as the exciton Bohr radius in GaP is smaller than 8 nm, no radial confinement is present in the 100 nm-thick nanowires. In addition, the lattice mismatch between WZ and ZB structures is very small, and the piezoelectric field $P_{\text{PZ}}$ is negligible compared to the spontaneous polarization field $P_{\text{SP}}$. The type-I band profile for the WZ/ZB/WZ GaP structures calculated using the 1D Schrödinger–Poisson method is presented in Figure 1b,c. The calculated electron and hole wave functions depicted in Figure 1b show a small overlap due to the presence of the ZB barrier, which implies a longer carrier lifetime. The energy corresponding to this spatially indirect transition depends on the barrier, which implies a longer carrier lifetime. The energy corresponding to this spatially indirect transition depends on the thickness of the ZB segment. Every addition of a ZB monolayer reduces the transition energy by an amount $\Delta E$, as shown in Figure 1d, enabling digital tuning of the GaP CPQW emission lines.

For optical characterization of CPQWs, WZ GaP nanowires incorporating multiple defect-free WZ/ZB/WZ homojunctions with atomically sharp interfaces were investigated. A representative WZ GaP nanowire of 100 nm diameter with multiple ZB segments is shown in the transmission electron microscopy (TEM) image in Figure 2a, where ZB sections with different lengths are separated by 200 nm long WZ segments. When considering the whole statistical ensemble of nanowires used for optical studies, ZB segments with lengths typically ranging between 3 and 60 MLs were investigated. As an example, ZB segments intentionally grown with lengths of 12 MLs and 33 MLs are shown in the high-resolution TEM (HRTEM) images in Figure 2b.c.

The optical emission of the CPQW is investigated using photoluminescence (PL) spectroscopy. For this study, a high density of nanowires is dispersed on a SiO$_2$/Si substrate, and the optical emission is collected while scanning across the nanowire ensemble. Three different PL spectra of GaP nanowires with CPQWs are shown in Figure 3a, together with one PL spectrum from a pure WZ GaP nanowire. The $\alpha$ and $\gamma$ peaks at 2.140 and 2.251 eV are related to bound excitons in WZ GaP, whereas the additional sharp emission lines appear in a spectral region below the $\gamma$-line. This spectral region does not show any emission lines in pure WZ GaP nanowires, clearly demonstrating that these peaks originate from the embedded CPQW segments. The CPQW emission lines show an average full width at half-maximum (fwhm) of 387 ± 13 $\mu$eV (see Figure 3b), reaching values as small as the setup resolution limit of about ∼200 $\mu$eV (see Supporting Information Figure S2). This line width is remarkably sharp for a III–V semiconductor QW and is the direct consequence of the presence of atomically sharp interfaces. Once inhomogeneous broadening due to interface roughness is absent, the remaining broadening mechanism is due to charge fluctuations, either due to nonresonant exciton in the CPQW barrier or due to charged impurities, which are unintentionally incorporated within the NW or at the NW surface. As a confirmation that the emission lines originate from the WZ sections of the CPQW, we performed polarization-dependent PL measurements on a single NW, as shown in the inset of Figure 3b. The emission from the CPQW is polarized perpendicular to the long nanowire c-axis (0001). This is in contrast to the isotropic behavior expected for carriers confined within a ZB GaP segment.

This observation strengthens the assumption of a type-I WZ/ZB junction with carrier confinement in the WZ segments, as predicted from band structure calculations. A clear indication of the presence of different CPQWs in the PL spectra of Figure 3a is the regular spacing between multiple emission lines. To determine the emission energies of segments with a specific thickness in view of the variable emission energy, we performed a statistical analysis of the emission energy of hundreds of nanowires with CPQWs as summarized in the histogram in Figure 3c. Due to the occasional presence of the bound exciton $\beta$-line at 2.164 eV in WZ GaP, the investigated energy range has been limited to 2.168–2.246
eV. Strikingly, from the multi-Gaussian peak fit of the histogram in Figure 3c, we observe up to 15 clear peaks, with additional peaks at 2.170 and 2.244 eV, with low statistical counts. The presence of peaks in the histogram clearly shows that the CPQW emission lines are not random but instead exhibit a constant spacing of $\sim$ 5 meV (see Figure 3d). This confirms that the position of the CPQW peaks is indeed governed by the respective number of ZB monolayers. Therefore, by tailoring the length of the ZB segments during growth, CPQWs emitting at the same energy can be designed with a high degree of control. Since the shortest ZB segment in a WZ wire has a length of 3 MLs, the first observable Gaussian peak should be associated with a ZB section of at least 3 MLs. The values for the standard deviation $\sigma_G$ of the Gaussian peaks are in the range of $1-5$ meV (see Figure 3c). We tentatively explain the increased broadening of the histogram peak with increasing barrier thickness by a non-negligible number of charged impurities located within the ZB barrier at our background impurity concentration of $6 \times 10^{17}$ cm$^{-3}$ (see below). Charged impurities will locally change the confinement potential resulting in fluctuations of the emission energy, as reported for stacking faults in GaN$^{36}$ or InP QDs.$^{37}$ We note that the standard deviation of $\sigma_G = 1-2$ meV for the shorter segments is comparable to state-of-the-art QD samples$^{38}$ and probably can be further reduced by lowering the background impurity concentration.

The constant spacing of $\sim$ 5 meV/ML is proportional with the polarization charge minus the compensating free charges due to background doping, which tend to accumulate near the ZB interface. For this reason, the energy shift per monolayer was calculated using the 1D Schrödinger–Poisson calculations as shown by the dashed line in Figure 3d. An unintentional background doping level of $6 \times 10^{17}$ cm$^{-3}$ as estimated from atom–probe tomography measurements on WZ GaP nanowires was considered in the model.$^{19}$ At this doping level, the calculations reproduce the experimentally observed trend for a spontaneous polarization of $P_{SP} = 4.6$ mC/m$^2$ (see Supporting Information S1 for more details). For a doping level of $1 \times 10^{17}$ cm$^{-3}$
(1 × 10^{18}) \text{cm}^{-3}$, the experimental data would be reproduced for a polarization value of 2.8 (5.5) mC/m$^2$, which gives an estimate of the accuracy of the derived value. As the charge distribution due to doping is not taken into account, the plate capacitor approximation is not fully sufficient—in contrast to GaN, where the spontaneous polarization is 5 times larger. A first calculation has been performed considering the WZ GaP bandgap of 2.19 eV, as shown by the green dashed line in Figure 3d. However, despite the agreement with the trend of the experimental data, a clear offset in energy is present. Therefore, we performed a second calculation considering the $\gamma$-line bound exciton level at 2.25 eV for the WZ phase. In this case, the resulting agreement with the experimental energies shows that the CPQW emission is related to a very efficient recombination channel associated with the localized $\gamma$-transition in WZ GaP. For comparison, the value we find for the spontaneous polarization $P_{\text{sp}}$ is slightly higher than the 3 mC/m$^2$ predicted by DFT calculations, but a factor of 2 lower than the estimate from the internal cell parameter $u$ measured by X-ray diffraction. 

Power-dependent PL measurements were performed on emission lines at different energies to confirm that the emissions originate from different CPQWs. The two CPQW peaks in Figure 4a are separated by 7.3 meV, which differs from the expected shift of ~5 meV for the addition/removal of a ZB ML (see Figure 3d) possibly due to local fluctuations in doping concentrations. Looking at the excitation power dependence of the PL intensity as shown in Figure 4b, a linear scaling with slope $\sim$ 1.0 is observed for both CPQW lines, followed by a saturation regime above 100 W/cm$^2$. Furthermore, the absence of a blue-shift of the emission energy with increasing power (see inset Figure 4b) indicates that the number of photogenerated carriers is very small compared to the number of polarization charges, thus avoiding a blue shift due to compensation of the spontaneous polarization field by the photoinjected carriers. As a confirmation of the carrier separation in CPQWs, we performed time-resolved PL (TRPL) measurements, as shown in Figure 4c. The measured lifetime for different CPQW emission lines ranges between 20 and 30 ns. A clear correlation between increase in lifetime with increasing emission energy was

Figure 4. (a) PL spectra from two different QWs with a difference in thickness of 1 ZB ML. (b) Integrated PL intensity as a function of the excitation power density for the peaks in panel a. Inset: peak energy as a function of the excitation power density. (c) Time-resolved PL measurements on a CPQW peak at 2.221 eV compared with the time decay for the $\gamma$-exciton line. (d) Integrated PL intensity as a function of the reciprocal temperature for a CPQW at 2.220 eV. The fit is performed considering one active nonradiative recombination channel. Inset: PL spectra for increasing temperature.
not observed. These values are much larger than the lifetime of 0.5–1.0 ns observed in WZ GaP in the same energy range and of the 0.70 ns lifetime for the γ-line. Since the charge carriers are spatially separated and the transition is across a quantum barrier, the overlap of the electron and hole wave functions is reduced, which results in a decrease of the oscillator strength for the CPQW transition and hence in an increase of the radiative lifetime. However, we note that the presence of nonradiative recombination channels could affect the estimation of the lifetime from TRPL measurements, limiting our observations to a more qualitative picture. When the temperature of the system is increased, the emission from the CPQWs is quenched due to the thermal escape of holes out of the WZ confinement potential, as shown in Figure 4d. From fitting the temperature dependence of the integrated PL intensity of a CPQW at 2.200 eV using a single nonradiative recombination channel, we find an activation energy $E_A = 82 \pm 16$ meV. In GaP, the WZ/ZB valence band offset is $\sim 135$ meV (see Figure 1), and considering the presence of quantized levels that reduce the energy barrier, the good agreement with $E_A$ confirms the confinement of both electrons and holes in the WZ segment of the CPQW.

In this work, we have provided experimental evidence for the presence of a spontaneous polarization in WZ GaP, which has a strong effect on the optical properties of crystal phase homojunctions in this material system. We demonstrated digital tuning of the emission energy associated with WZ–ZB–WZ crystal phase quantum well structures by tailoring the length of the ZB segments. This approach will allow the controlled fabrication of multiple CPQDs emitting identical photons. Identical single photon emitters are a key ingredient for the realization of entangled states in quantum information processing.

**Notes**

The authors declare no competing financial interest.

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**REFERENCES**

(14) Bolinsson, J.; Caroff, P.; Mandl, B.; Dick, K. A. Nanotechnology 2011, 22 (26), 265606.